N-Channel 100-V (D-S) MOSFET

Key Features:

- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

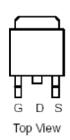
Typical Applications:

- · LED Inverter Circuits
- DC/DC Conversion Circuits
- Motor drives

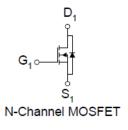
PRODUCT SUMMARY				
V _{DS} (V)	$r_{DS(on)}(m\Omega)$	I□ (A)		
100	5.5 @ V _{GS} = 10V	200 ^a		
100	$7 @ V_{GS} = 6.5V$	200		



FREE



TO-263



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)							
Parameter			Limit	Units			
Drain-Source Voltage			100	V			
Gate-Source Voltage	V_{GS}	±20	V				
Continuous Drain Current a	T _C =25°C	I _D	200	Α			
Pulsed Drain Current ^b		I _{DM}	400	Α			
Continuous Source Current (Diode Conduction) a	T _C =25°C	I _S	200	Α			
Power Dissipation ^a	T _C =25°C	P_{D}	300	W			
Operating Junction and Storage Temperature Range		T_J , T_{stg}	-55 to 175	°C			

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	Maximum	Units			
Maximum Junction-to-Ambient °	$R_{\theta JA}$	62.5	°C/W			
Maximum Junction-to-Case	$R_{\theta JC}$	0.5	C/VV			

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Notes

- a. Package Limited
- b. Pulse width limited by maximum junction temperature
- c. Surface Mounted on 1" x 1" FR4 Board.

Electrical Characteristics

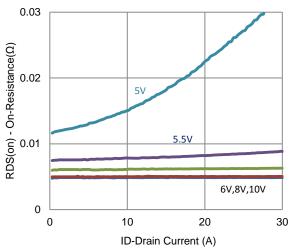
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit		
Static								
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \text{ uA}$	1			V		
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA		
Zero Gate Voltage Drain Current		$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}$			1 uA			
Zero Gate Voltage Brain Current	I _{DSS}	$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$	$0 \text{ V, T}_{\text{J}} = 55^{\circ}\text{C}$ 10			uA		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	120			Α		
Drain Cauras On Basistanas a	r	$V_{GS} = 10 \text{ V}, I_{D} = 20 \text{ A}$			5.5	mΩ		
Drain-Source On-Resistance ^a	r _{DS(on)}	$V_{GS} = 6.5 \text{ V}, I_D = 16 \text{ A}$			7	11122		
Forward Transconductance a	g _{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 20 \text{ A}$		15		S		
Diode Forward Voltage ^a	V_{SD}	$I_{S} = 20 \text{ A}, V_{GS} = 0 \text{ V}$		0.88		V		
		Dynamic ^b						
Total Gate Charge	Q_g	$V_{DS} = 50 \text{ V}, V_{GS} = 6.5 \text{ V},$		159		nC		
Gate-Source Charge	Q_{gs}	$I_{D} = 20 \text{ A}$		39				
Gate-Drain Charge	Q_gd	1D = 20 A		88				
Turn-On Delay Time	t _{d(on)}	$V_{DS} = 50 \text{ V}, R_1 = 2.5 \Omega,$		32				
Rise Time	t _r	$V_{DS} = 50 \text{ V}, N_L - 2.5 \Omega,$ $I_D = 20 \text{ A},$		88		ns		
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = 10 \text{ V}, R_{GEN} = 1.5 \Omega$		151				
Fall Time	t _f	V GEN = 10 V, T GEN = 1.0 12		50				
Input Capacitance	C _{iss}			11094				
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		900		pF		
Reverse Transfer Capacitance	C_{rss}			894				

Notes

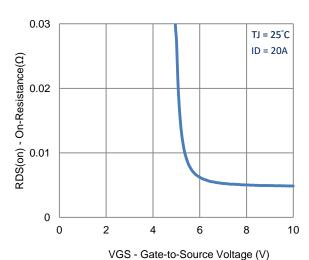
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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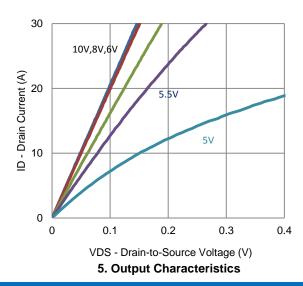
Typical Electrical Characteristics

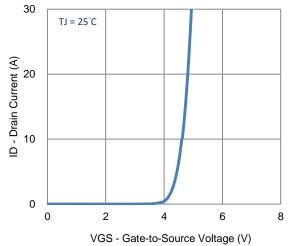


1. On-Resistance vs. Drain Current

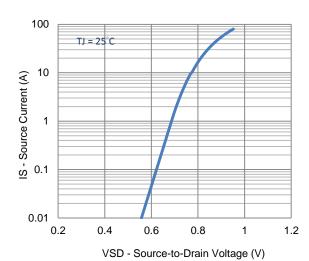


3. On-Resistance vs. Gate-to-Source Voltage

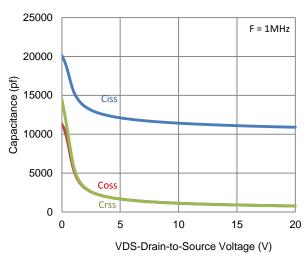




2. Transfer Characteristics

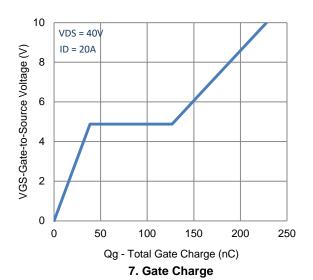


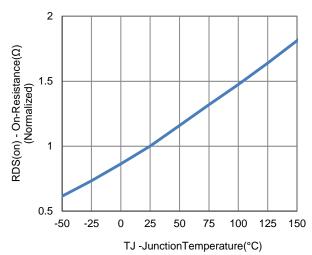
4. Drain-to-Source Forward Voltage



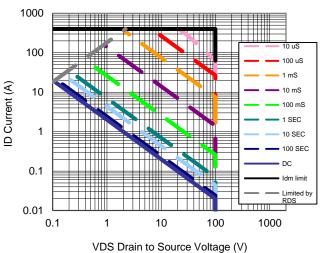
6. Capacitance

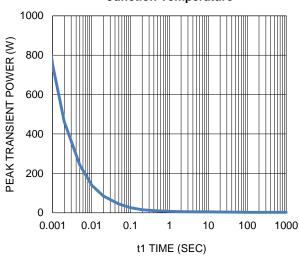
Typical Electrical Characteristics





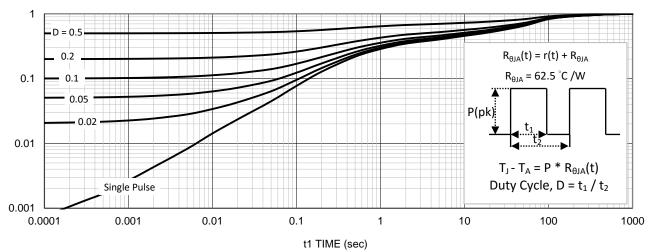
8. Normalized On-Resistance Vs Junction Temperature





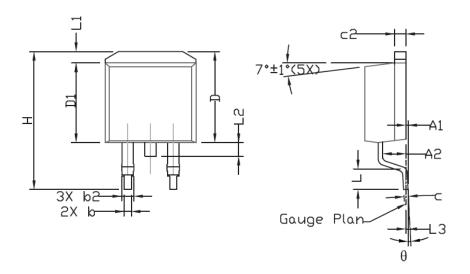
9. Safe Operating Area

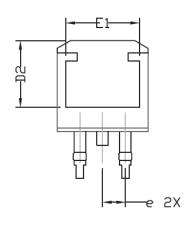
10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

Package Information





CVAREI	DIMENS:	IONAL F	REQMTS	INCH	ES REG	2TM	
SYMBOL	MIN	NDM	MAX	MIN	NDM	MAX	
Α	4,30	4.57	4,72	0.169	0.180	0.186	
A1	0		0,25	0		0.010	
A2	2,47	2.57	2,67	0.097	0.101	0.105	
b	0.69	0,813	0.94	0.027	0.032	0.037	
b2	1.17	1.27	1,45	0.046	0.050	0.057	
С	0.48	0,50	0,60	0.019	0.020	0.024	
c2	1,17	1.27	1.37	0.046	0,050	0,054	
D	9,80	10.05	10,30	0.386	0,396	0.406	
D1	8,64	8.78	9,65	0,340	0,346	0,380	
D2	7.12	7.37	7,62	0.280	0.290	0,300	
E	9,70	10.15	10,54	0,382	0,400	0.415	
E1	8,00	8,20	8,40	0,315	0,323	0.331	
е	2.54 BSC			0.	0.100 BSC		
H	14,99	15,24	15,49	0.590	0.600	0.610	
L	1,78	2.29	2.79	0.070	0.090	0.110	
L1	1.02	1.27	1.52	0.040	0.050	0,060	
L2			1,75			0.069	
L3		0,254			0.010		
θ	0.		8•	0°		8*	